

The effects of high-energy proton irradiation on the electrical characteristics of Au/Ni/4H-SiC Schottky barrier diodes



E. Omotoso^{a,b,*}, W.E. Meyer^a, P.J. Janse van Rensburg^a, E. Igumbor^a, S.M. Tunhuma^a, P.N.M. Ngoepe^a, H.T. Danga^a, F.D. Auret^a

^a Department of Physics, University of Pretoria, Private Bag X20, Hatfield 0028, South Africa

^b Department of Physics, Obafemi Awolowo University, Ile-Ife 220005, Nigeria

ARTICLE INFO

Article history:

Received 8 December 2016

Received in revised form 22 May 2017

Accepted 23 May 2017

Available online 31 May 2017

Keywords:

Richardson constant

Proton irradiation

4H-SiC

SBD

ABSTRACT

Au/Ni (20:80) Schottky barrier diodes (SBDs) were resistively evaporated on nitrogen-doped *n*-type 4H-SiC. Current-voltage (*I*-*V*) and capacitance-voltage (*C*-*V*) characteristics of the SBDs were investigated before and after bombardment with 1.8 MeV proton irradiation at a fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$. The measurements were carried out in the temperature range 40–300 K in steps of 20 K. Results obtained at room temperature (300 K) showed highly rectifying devices before and after bombardment. It was observed that the proton irradiation induced an increase of ideality factor from 1.05 to 1.13, a decrease in Schottky barrier height from 1.40 to 1.22 eV, an increase in series resistance from 10 to 66 Ω and a noticeable increase of the saturation current from 3.0×10^{-21} to 6.8×10^{-17} A. The increase in saturation current after proton irradiation was attributed to the presence of interfacial states created by irradiation-induced defects. Thermionic emission dominated the *I*-*V* characteristics in the temperature range 120–300 K but the *I*-*V* characteristics deviated from thermionic emission theory at temperatures below 120 K for devices both before and after irradiation. The variation of the SBDs characteristics with temperature was attributed to the presence of lateral inhomogeneities of the SBH. Modified Richardson constants were determined from a Gaussian distribution of barrier heights to be 133 and 165 $\text{A cm}^{-2} \text{ K}^{-2}$ before and after irradiation, respectively.

© 2017 Elsevier B.V. All rights reserved.

1. Introduction

A Schottky barrier diode (SBD) is a metal semiconductor device that is widely used where diodes with low forward voltage drop, junction capacitance and very fast switching speeds are required. This makes SBDs ideal for use as rectifiers in photovoltaic systems, high-efficiency power supplies and high frequency oscillators [1]. In addition, SBDs have important use in optoelectronics, high frequency and bipolar integrated circuits applications [2]. The reliability of the diodes depends on the quality of the metal-semiconductor (M-S) junction [3]. The performance of SBDs may be quantified experimentally in terms of ideality factor, Schottky barrier height (SBH), saturation current and series resistance. Among these properties of the M-S interface, SBH plays a major role in the successful operation of many devices in transporting electrons across the M-S junction [4]. To extract the SBH from the *I*-*V* characteristics, the value of the Richardson constant is needed.

The Richardson constant is one of the most important parameters in the thermionic emission theory of current transport across M-S junctions. Here, it is the proportionality constant in the relationship between the current and the voltage for the flow of electrons across the M-S junction. The theoretical value of the effective Richardson constant of 4H-SiC reported in literature is $146 \text{ A cm}^{-2} \text{ K}^{-2}$ [5], which differs significantly from the experimentally observed values due to various factors. The factors responsible for deviation may be small active area of devices and atomic or barrier inhomogeneities at the M-S interface, which are caused by defects, multiple phases and grain boundaries.

The 4H polytype of SiC has a wide band gap of 3.26 eV [6], and a promising material for vertical type high-voltage devices due to its higher bulk mobility and smaller anisotropy. Due to its capability to operate at a very high temperature, high power and high frequency, it is a suitable substrate material for producing high power, high frequency electronic devices. Also, due to its radiation hardness, SiC has many applications in radiation harsh environments, such as space, accelerator facilities and nuclear power plants [7]. The effects of radiation and temperature on semiconductor devices are scientifically significant for radiation sensing

* Corresponding author at: Department of Physics, University of Pretoria, Private Bag X20, Hatfield 0028, South Africa.

E-mail address: ezekiel.omotoso@up.ac.za (E. Omotoso).

applications, as well as technologically important for manufacturing processes and high temperature and high power applications [8].

Experimental and theoretical studies of defects in semiconductors have been reported [8–12], but room temperature I - V and C - V measurements characteristics alone cannot provide comprehensive information about the mechanisms responsible for the formation of a barrier at the junction of the M-S and electrical properties of SBDs [13]. More information about diodes is revealed by characterising them over a wide temperature range (40 – 300 K).

In the previous studies, the radiation hardness of some wide bandgap semiconductors, such as SiC, ZnO and GaN, that make them suitable for use in radiation environments has been studied [14]. We have reported the influence of alpha-particle and high energy electron irradiation on the electrical characteristics of 4H-SiC measured at different temperatures [8,12]. To the best of our knowledge, the effect of 1.8 MeV proton irradiations at fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$ on Au/Ni/4H-SiC SBDs has not been reported.

In this work, we report the effect of 1.8 MeV proton bombardment on the electrical characteristics of nitrogen-doped, n -type 4H-SiC SBDs measured over a wide temperature range (40–300 K). The major aim of this work was to determine the extent to which the characteristics of Au/Ni contacts on n -type 4H-SiC would be affected by proton irradiations with 1.8 MeV measured at different cryogenic temperatures.

2. Experimental details

A nitrogen-doped, n -type 4H-SiC wafer supplied by Cree Research Inc. was used for this study. The epilayer was grown by chemical vapour deposition. It was polished on both sides with the Si-face epi ready with resistivity of $0.02 \Omega\text{-cm}$ and doping density of $1.6 \times 10^{16} \text{ cm}^{-3}$. Samples were cut into smaller sizes from the wafer. Before metallization of the ohmic contact on the highly doped side ($1.0 \times 10^{18} \text{ cm}^{-3}$) of the sample, degreasing and etching were carried out as described in Refs. [8,12,15,16]. Nickel ohmic contacts of 300 nm in thickness were thermally evaporated at a deposition rate of $\sim 0.09 \text{ nm s}^{-1}$ and vacuum pressure of $\sim 2 \times 10^{-5} \text{ mbar}$. The ohmic contacts were annealed in a quartz tube heated by a Linderberg Hevi-Duty furnace in flowing Ar at 950°C for 10 min to reduce the contact (metal-semiconductor) resistance by the forming of nickel silicide. Prior to Schottky contact evaporation on the front (epi-layer) side of the samples, the samples were degreased as reported in Refs. [8,12,15,16]. Au/Ni Schottky contacts, 0.6 mm in diameter with a thickness of 200/800 nm, were thermally evaporated through a metal contact mask at very low deposition rate of $\sim 0.02 \text{ nm s}^{-1}$ and vacuum pressure of $\sim 1 \times 10^{-5} \text{ mbar}$.

The suitability of the contacts was tested immediately after evaporation by characterizing them using an I - V and C - V system comprising an HP 4140 B pA Meter/DC Voltage Source and an HP 4192A LF Impedance Analyzer, respectively. The characterization of the samples was done at room temperature and in the dark.

Thereafter, the sample was placed under vacuum in a closed cycle helium cryostat and the I - V and C - V measurements were carried out on a particular SBD in the temperature range of 40–300 K in intervals of 20 K under control of a program written in LabviewTM.

After I - V and C - V measurements, the same SBD was bombarded at room temperature under a high vacuum with 1.8 MeV protons from a Van de Graaff accelerator. The diode received a fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$. Immediately after proton irradiation, the contact quality was evaluated using current-voltage-temperature and capacitance-voltage-temperature measurements. The experiment

was repeated on other diodes for confirmation of the results observed.

3. Results and discussion

3.1. Current-voltage characteristics

The suitability of the Au/Ni/4H-SiC contacts for temperature dependent I - V studies before and after proton irradiation was confirmed from the results obtained at room temperature as shown in Figs. 1. Some of the important electrical parameters such as ideality factor (n), Schottky barrier height (ϕ_{B}), series resistance (R_s) and saturation current (I_s) obtained from the measurements are summarized in Table 1. The ideality factor determined from the slope of the linear region of the semi-log I - V characteristics was close to unity and the SBH evaluated from the intercept was relatively high, which shows that thermionic emission (TE) model sufficiently described the current flow from Au/Ni to 4H-SiC. We concluded that the Au/Ni/4H-SiC SBDs were highly rectifying and thus suitable for temperature dependent measurements. A significant deviation was observed after proton irradiation at fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$. The deviation was as a result of the increase of deep level defect density at the interface with irradiation [8,12,15,17].

Fig. 1 shows the semi-logarithmic forward bias I - V characteristics of the SBDs before and after proton irradiation measured over the temperature range 40–300 K. The plots before and after proton irradiation were linear up to a current of $\sim 10^{-4} \text{ A}$, but deviated below 80 K. The deviation of the plots from linearity at high forward voltages may be due to series resistance caused by the interfacial layer between Au/Ni and 4H-SiC, and the bulk of the material. From Fig. 1, the I - V plots show lower current at lower temperature, which is in accordance with thermionic emission-diffusion theory [18]. It was also observed that the decrease of the forward bias current with decrease in temperature was less pronounced after irradiation, which was attributed to the presence of interfacial states created by irradiation-induced defects [15,19].

The linear part of the plots was fitted over the forward voltage range, where thermionic emission was the dominant transport mechanism. From the fits, the important electrical parameters that give better understanding of the devices performance at different temperatures were determined according to Eqs. (1) and (2) as reported in Refs. [3,8,12,20–22].

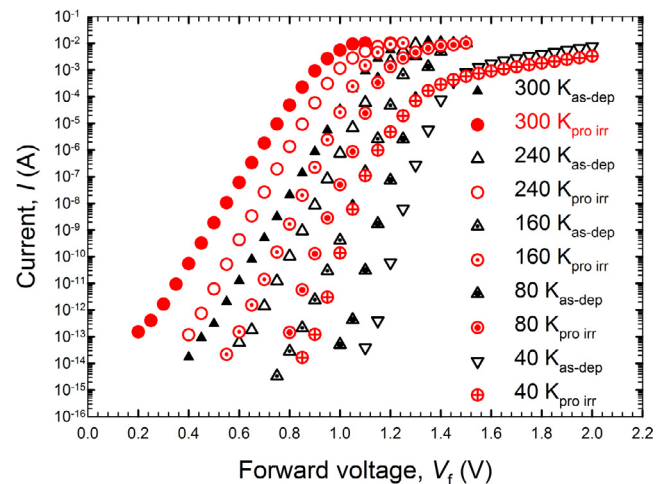


Fig. 1. Semi-logarithmic forward I - V characteristics of Au/Ni/4H-SiC Schottky diodes before and after proton irradiation at a fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$, measured at different temperatures between 40 K and 300 K.

Table 1Electrical properties of Au/Ni/n-type 4H-SiC SBDs before and after 1.8 MeV proton irradiation determined from *I*-*V* and *C*-*V* characteristics at 40 and 300 K, respectively.

SBD	<i>n</i>	<i>I_s</i> (A)	<i>R_s</i> (Ω)	<i>N_d</i> - <i>N_a</i> (× 10 ¹⁶ cm ⁻³)	<i>V_{bi}</i> (V)	Φ _{I-V} (eV)	Φ _{C-V} (eV)
As-deposited (300 K)	1.05	3.0 × 10 ⁻²¹	10	1.68	1.16	1.40	1.42
As-deposited (40 K)	3.51	2.9 × 10 ⁻⁴⁵	66	1.30	2.68	0.45	2.71
Proton irradiation (300 K) [*]	1.13	6.8 × 10 ⁻¹⁷	25	1.62	1.04	1.22	1.30
Proton irradiation (40 K) [*]	4.45	5.4 × 10 ⁻³⁹	160	1.22	3.23	0.34	3.26

^{*} At fluence of 2.0 × 10¹² cm⁻² (300 K).

$$I = I_s \left[\exp\left(\frac{qV}{nkT}\right) - 1 \right] \quad (1)$$

$$I_s = AA^* T^2 \exp\left(-\frac{q\phi_{ap}}{kT}\right) \quad (2)$$

where *I* is the current flowing through the diode in forward voltage, *I_s* is the saturation current measured at zero voltage, *q* is the electronic charge, *V* is the applied voltage, *n* is the ideality factor, *k* is the Boltzmann constant, *T* is the temperature in Kelvin, *A* is the area of Schottky barrier diode, *A*^{*} is effective Richardson constant and *φ_{ap}* is the experimental apparent SBH. Table 1 compares the results obtained from the SBDs at 300 K and 40 K before and after irradiation.

Gradual changes in ideality factor and SBH_{I-V} before and after irradiation were observed from 120 to 300 K but the temperature dependence became more significant below 120 K as shown in Fig. 2. This temperature dependence of the ideality factor and SBH_{I-V} is in agreement with results observed after alpha-particle and high-energy electron irradiation [8,12], and is ascribed to deviation from thermionic emission theory at lower temperatures (<120 K). This deviation may be ascribed to an inhomogeneous barrier at the interface. The deviation from ideality was more pronounced after irradiation, which was due to the presence of additional deep level defects induced by irradiation as already observed in Refs. [8,12].

3.2. Capacitance-voltage characteristics

Fig. 3 shows the plot of 1/*C*² versus voltage of the SBDs before and after proton irradiation at fluence of 2.0 × 10¹² cm⁻² measured at 1 MHz for temperatures 40, 80 and 300 K. These temperatures were chosen since there was little or no significant change from 100 to 300 K before and after irradiation. As seen from Fig. 3, at room temperature, the capacitance of the irradiated diodes was less than that of the unirradiated diodes. At lower temperatures,

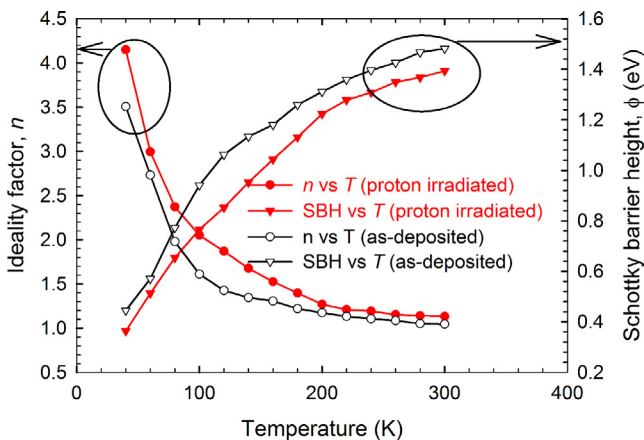


Fig. 2. Comparison of ideality factor, *n*, and Schottky barrier height, *φ*, as function of temperature before and after 1.8 MeV proton irradiation at fluence of 2.0 × 10¹² cm⁻² at temperature range 40–300 K.

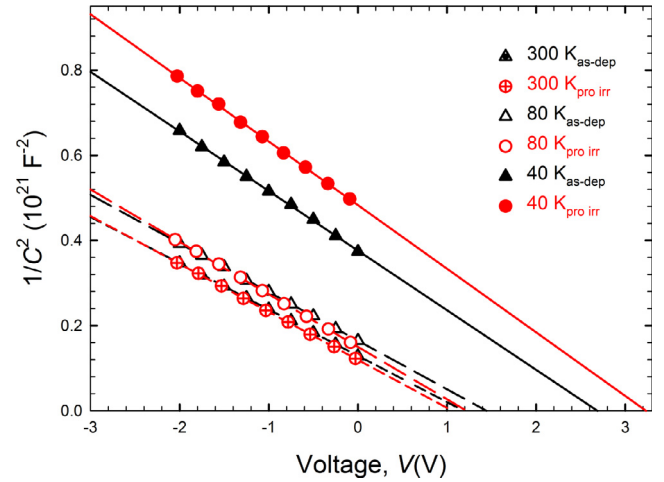


Fig. 3. Graph of *C*⁻² as a function of voltage of a Au/Ni/4H-SiC SBD before and after 1.8 MeV proton irradiation at fluence of 2.0 × 10¹² cm⁻² measured at different temperatures between 40 and 300 K.

the capacitance decreased and the difference between the irradiated and unirradiated samples increased. The electrical parameters such as SBH_{C-V} (determined from the intercept), net donor concentration, *N_d* - *N_a* (determined from the slope) and built-in voltage, *V_{bi}* (evaluated from the intercept of x-axis) were calculated from the plots of 1/*C*² vs *V* according to Refs. [3,8,12,20,21] and are shown in Table 1. As listed in Table 1, the SBH_{C-V} increases with decreasing temperature though lower after irradiation. The values of SBH_{C-V} obtained were higher than those of SBH_{I-V} which can be attributed to inhomogeneity in the interface oxide layer composition, non-uniformity of the interfacial layer thickness, distribution of interface charges, impurity level and quantum mechanical tunnelling among other reasons [8]. In addition, the net donor concentration decreases slightly with decreasing temperature. The values SBH_{C-V} were lower after irradiation which might be as a result of an increased tapping of charge due to the induced deep level defects.

The room temperature change in carrier concentration, Δ(*N_d* - *N_a*), of the SBD determined before irradiation (1.68 × 10¹⁶ cm⁻³) and after proton irradiation (1.62 × 10¹⁶ cm⁻³) was calculated to be 6 × 10¹⁴ cm⁻³. The carrier removal rate, *η*, after the fluence, *φ*, of 2.0 × 10¹² cm⁻² was calculated according to Eq. (3) [8,12].

$$\eta = \frac{\Delta(N_d - N_a)}{\phi} \quad (3)$$

From Eq. (3), the carrier removal rate due to proton irradiation of the SBDs with energy of 1.8 MeV was calculated to be 300 cm⁻¹.

3.3. Barrier height inhomogeneities analysis

The anomalous behaviour (i.e. increase in SBH with increasing temperature) that occurred in the forward *I*-*V* measurements at different temperatures has been reported [8,12,23]. Werner and Guttler suggested that the non-ideal behaviour can be best

explained by spatial distribution of the SBH at the interface of M-S Schottky contacts. This anomaly can be described by assuming the Gaussian distribution, $P(\phi_B)$, with a standard deviation, σ_s , and a mean SBH, ϕ_{B0} , as written in Eq. (4) [24].

$$P(\phi_B) = \frac{1}{\sigma_s \sqrt{2\pi}} \exp\left(-\frac{(\phi_B - \phi_{B0})^2}{2\sigma_s^2}\right) \quad (4)$$

From the Gaussian distribution of the SBH, the experimental apparent SBH ϕ_{ap} at zero bias can be expressed as:

$$\phi_{ap} = \phi_{B0}(T=0) - \frac{q\sigma_{s0}^2}{2kT} \quad (5)$$

where $\phi_{B0}(T=0)$ is the mean SBH at zero bias which was evaluated from the intercept of Fig. 4 (i.e. is the SBH extrapolated to zero temperature), σ_{s0} is the standard deviation at zero bias which was determined from the slope of Fig. 4 [25].

Fig. 4 shows the plot of experimental value of ϕ_{ap} as a function of $1/(2kT)$ before and after proton irradiation. From the plot, the $\phi_{B0}(T=0)$ was determined from the intercept to be 1.71 and 1.44 eV, and the σ_{s0} (which is a measure of barrier homogeneity) was estimated from the slope as 0.116 and 0.113 eV before and after irradiation, respectively. The value of σ_{s0} describes the magnitude of the SBH's homogeneity at the interface of the diodes [4]. Since the values of σ_{s0} is not small compared to the values of $\phi_{B0}(T=0)$, we conclude the presence of barrier inhomogeneity at the interface of Au/Ni/4H-SiC SBDs [4]. This barrier inhomogeneity influence low temperature I - V characteristics, as low barrier regions conduct a greater fraction of the current at lower temperatures, thereby causing a lower barrier to be measured.

The inhomogeneous barrier height and deviation from thermionic emission and diffusion theory have been predicted from the temperature dependent behaviour of the ideality factor and SBH plotted in Fig. 4. The standard deviation of the barrier height, σ_{s0} , plays a major role in correcting the values of Richardson constant determined from the conventional Richardson's plot as reported in Ref. [8]. The conventional (homogeneous SBH) Richardson constant and barrier height can be determined by re-written Eq. (2) as given in Eq. (6).

$$\ln\left(\frac{I_s}{T^2}\right) = \ln(AA^*) - \frac{q\phi_B}{kT} \quad (6)$$

Fig. 5 depicts the plot of $\ln(I_s/T^2)$ as a function of $1000/T$, where the effective Richardson constant and SBH were determined. We calculated the effective Richardson constant, A^* , from the intercept

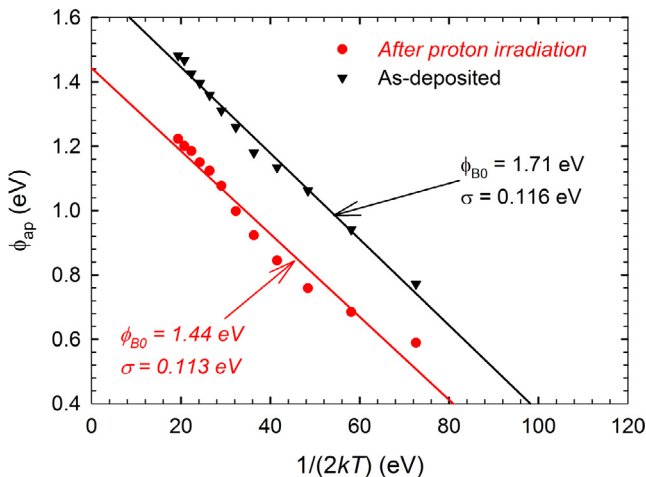


Fig. 4. The zero bias apparent barrier height versus $1/2kT$ for the Au/Ni/4 H-SBDs before and after proton irradiation.

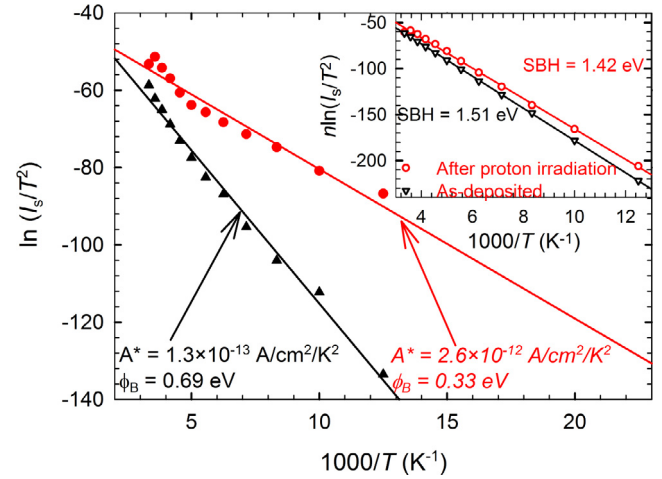


Fig. 5. The Richardson plot, $\ln(I_s/T^2)$ versus $1000/T$, for Au/Ni/4H-SiC before and after 1.8 MeV proton irradiation at of fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$. The insert shows the plot of $n[\ln(I_s/T^2)]$ versus $1000/T$ to linearize the main plot.

of the plot to be 1.3×10^{-13} and $2.6 \times 10^{-12} \text{ A cm}^{-2} \text{ K}^{-2}$ before and after proton irradiation, respectively. These experimental values were very small compared to the theoretical value of effective Richardson constant of $146 \text{ A cm}^{-2} \text{ K}^{-2}$. This deviation may be due to the effect of Schottky barrier inhomogeneity at the interface between metal and semiconductor as well as crystal defects and potential fluctuation. It may also be an indication that the active area is smaller than the actual devices area, but this effect could not explain such a large deviation.

The extremely small value of the Richardson can be corrected by taking the inhomogeneity of the SBH into account, in which case Eq. (6) becomes:

$$\ln\left(\frac{I_s}{T^2}\right) - \left(\frac{q^2\sigma_{s0}^2}{2k^2T^2}\right) = \ln(AA^{**}) - \frac{\phi_{B\text{modified}}}{kT} \quad (7)$$

From Eq. (7), modified Richardson plot of $\ln(I_s/T^2) - (q^2\sigma_{s0}^2/2k^2T^2)$ versus $1000/T$ before and after proton irradiation were obtained and plotted in Fig. 6. The mean barrier height, ϕ_{B0} , was calculated by equating the gradient to $q\phi_B/k$. After substitution, the values of $\phi_{B\text{modified}}$ were determined to be 1.71 and 1.46 eV for as deposited and proton irradiated SBDs, respectively. As noticed, the modified mean barrier heights calculated were

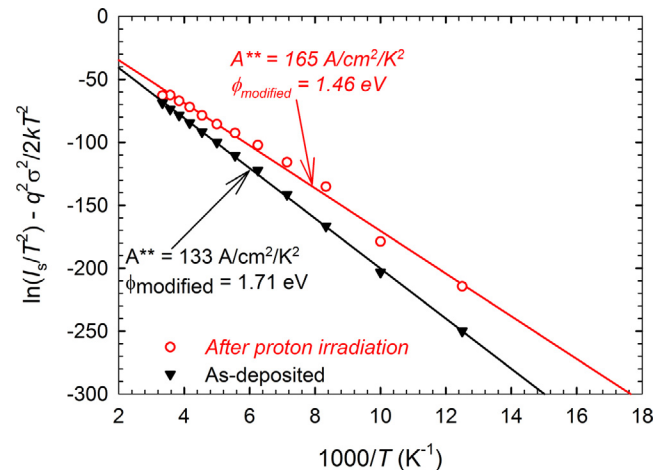


Fig. 6. The modified Richardson plot for the Au/Ni/4H-SiC SBDs before and after proton irradiation.

Table 2The characteristics of Ni/Au SBDs on *n*-4H-SiC before and after 1.8 MeV proton irradiation.

Samples	$\sigma_{so}(\text{eV}) \pm 0.001$	$\phi_{B0}(T=0) (\text{eV}) \pm 0.01$	$\phi_{B\text{modified}}(\text{eV}) \pm 0.01$	$A^* (\text{A cm}^{-2} \text{K}^{-2})$	$A^{**} (\text{A cm}^{-2} \text{K}^{-2})$
As-deposited	0.116	1.71	1.71	1.3×10^{-13}	133
After proton irradiation	0.114	1.44	1.46	2.6×10^{-12}	165

approximately equal to those obtained from the plot of ϕ_{ap} vs $1/2kT$ in Fig. 4. In addition, the modified Richardson constants, A^{**} , were determined by equating the intercept to $\ln(AA^{**})$. The values of A^{**} for Au/Ni/4H-SiC SBDs before and after proton irradiation were calculated to be 133 and 165 $\text{A cm}^{-2} \text{K}^{-2}$, respectively, which is in good agreement with the theoretical value. The values of A^{**} obtained were in line with what has been observed during alpha-particle [12] and high-energy electron irradiation [8]. In addition, the calculated results of ϕ_{B0} and A^{**} before and after irradiation as shown in Table 2, revealed the extent to which Au/Ni/4H-SiC SBDs could be affected by high-energy proton irradiation at a fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$. From these results, a conclusion was reached that 4H-SiC is a radiation hard semiconductor that is suitable to operate at high radiation harsh environments.

4. Summary and conclusions

We have successfully fabricated highly rectifying Au/Ni/4H-SiC SBDs by thermal evaporation techniques. The influence of proton irradiation at a fluence of $2.0 \times 10^{12} \text{ cm}^{-2}$ on the Schottky contacts has been investigated by *I*-*V* and *C*-*V* characteristics at cryogenic temperatures from 40 to 300 K. The electrical behaviour of the devices before and after proton irradiation revealed good Schottky contacts that support the suitability of SiC in high radiation environments. The performance of the devices deviated from thermionic emission at temperatures below 120 K. This deviation could be well explained by barrier inhomogeneities that formed at the interface of Au/Ni and 4H-SiC which were described by assuming a Gaussian distribution of SBHs. The deviation was more pronounced after proton irradiation because of deep level defects induced into the Schottky barrier diodes as a result of bombardment. By using a Gaussian distribution of barrier heights, the modified Richardson constants before and after high-energy proton irradiation were 133 and 165 $\text{A cm}^{-2} \text{K}^{-2}$, respectively, which is much closer to the theoretical value obtained when a homogeneous barrier height is assumed. It has been confirmed from our findings that the Richardson constant is not dependent on the Schottky barrier height and active devices only, but also depend on the irradiation types. The findings revealed that the Richardson constant might be influenced by irradiation. We conclude that the *I*-*V* characteristics of both irradiated and unirradiated Au/Ni/4H-SiC Schottky diodes are well described a Gaussian distribution of Schottky barrier height.

Acknowledgements

The authors would like to acknowledge the financial support of the University of Pretoria. This work is based on research supported by the National Research Foundation (NRF) of South Africa, Grant number 98961. The Grant-holders acknowledge that opinions expressed, findings and conclusions arrived at, are those of the authors and are not necessarily to be attributed to the NRF.

References

- [1] A. Elasser, M.H. Kheraluwala, M. Ghezzi, R.L. Steigerwald, N.A. Evers, J. Kretschmer, T.P. Chow, A comparative evaluation of new silicon carbide diodes and state-of-the-art silicon diodes for power electronic applications, *Ind. Appl. IEEE Trans.* 39 (4) (2003) 915–921.
- [2] A.F. Özdemir, A. Turut, A. Kökçe, The double Gaussian distribution of barrier heights in Au/n-GaAs Schottky diodes from *I*–*V*–*T* characteristics, *Semicond. Sci. Technol.* 21 (3) (2006) 298.
- [3] E. Rhoderick, R. Williams, *Metal-Semiconductor Contacts*, second ed., Clarendon, Oxford Science, Oxford, 1988.
- [4] V. Janardhanam, A. Ashok Kumar, V. Rajagopal Reddy, P. Narasimha Reddy, Study of current-voltage-temperature (*I*-*V*-*T*) and capacitance-voltage-temperature (*C*-*V*-*T*) characteristics of molybdenum Schottky contacts on n-InP (1 0 0), in: *J. Alloys Compd.* 485 (1–2) (2009) 467–472.
- [5] Z. Ouennoughi, S. Toumi, R. Weiss, Study of barrier inhomogeneities using *I*-*V*-*T* characteristics of Mo/4H-SiC Schottky diode, *Physica B* 456 (2015) 176–181.
- [6] L.M. Tolbert, B. Ozpineci, S.K. Islam, M.S. Chinthavali, Wide bandgap semiconductors for utility applications, *Power Energy Syst. Proc.* 1 (2003) 317–321.
- [7] V. Kazukauskas, J.-V. Vaitkus, Influence of defect traps and inhomogeneities of SiC crystals and radiation detectors on carrier transport, *Opto-Electron. Rev.* 12 (4) (2004) 377–382.
- [8] E. Omotoso, W.E. Meyer, F.D. Aurret, A.T. Paradzah, M. Diale, S.M.M. Coelho, P.J. Janse van Rensburg, The influence of high energy electron irradiation on the Schottky barrier height and the Richardson constant of Ni/4H-SiC Schottky diodes, *Mater. Sci. Semicond. Process.* 39 (2015) 112–118.
- [9] E. Igumbor, R.E. Mapasha, R. Andrew, W.E. Meyer, A first principle hybrid functional calculation of $\text{TM}^{3+}\text{Ge}-\text{V}_{\text{Ge}}$ defect complexes in germanium, *Comput. Condens. Matter* 8 (2016) 31–35.
- [10] E. Igumbor, W.E. Meyer, A hybrid functional calculation of TM^{3+} defects in germanium (Ge), *Mater. Sci. Semicond. Process.* 43 (2016) 129–133.
- [11] S.M.M. Coelho, F.D. Aurret, P.J. Janse van Rensburg, J.M. Nel, Electrical characterization of defects introduced in n-Ge during electron beam deposition or exposure, *J. Appl. Phys.* 114 (17) (2013) 1737081–1737088.
- [12] E. Omotoso, W.E. Meyer, F.D. Aurret, A.T. Paradzah, M. Diale, S.M.M. Coelho, P.J. Janse van Rensburg, P.N.M. Ngoepe, Effects of 5.4 MeV alpha-particle irradiation on the electrical properties of nickel Schottky diodes on 4H-SiC, *Nucl. Instrum. Methods Phys. Res. Sect. B: Beam Interact. Mater. Atoms* 365 (2015) 264–268, Part A.
- [13] S. Zeyrek, M.M. Bulbul, S. Altindal, M.C. Baykul, H. Yuzer, The double gaussian distribution of inhomogeneous barrier heights in Al/GaN/p-GaAs (MIS) Schottky diodes in wide temperature range, *Braz. J. Phys.* 38 (4) (2008) 591–597.
- [14] J. Grant, W. Cunningham, A. Blue, V. O'Shea, J. Vaitkus, E. Gaubas, M. Rahman, Wide bandgap semiconductor detectors for harsh radiation environments, *Nucl. Instrum. Methods Phys. Res., Sect. A* 546 (1–2) (2005) 213–217.
- [15] E. Omotoso, W.E. Meyer, F.D. Aurret, M. Diale, P.N.M. Ngoepe, Response of Ni/4H-SiC Schottky barrier diodes to alpha-particle irradiation at different fluences, *Physica B* 480 (2016) 196–200.
- [16] A.T. Paradzah, F.D. Aurret, M.J. Legodi, E. Omotoso, M. Diale, Electrical characterization of 5.4 MeV alpha-particle irradiated 4H-SiC with low doping density, *Nucl. Instrum. Methods Phys. Res., Sect. B* 358 (2015) 112–116.
- [17] K. Çınar, C. Coşkun, Ş. Aydoğan, H. Asil, E. Gür, The effect of the electron irradiation on the series resistance of Au/Ni/6H-SiC and Au/Ni/4H-SiC Schottky contacts, *Nucl. Instrum. Methods Phys. Res., Sect. B* 268 (6) (2010) 616–621.
- [18] A. Chawanda, W. Mtangi, F.D. Aurret, J. Nel, C. Nyamhere, M. Diale, Current-voltage temperature characteristics of Au/n-Ge (1 0 0) Schottky diodes, *Physica B* 407 (10) (2012) 1574–1577.
- [19] Y. Sundarasaradula, P. Sodhgam, N. Klunngien, W. Titiroongruang, Temperature dependence of electrical characteristics on pn junction power diodes irradiated by X-ray, *Electrical Engineering/Electronics, Computer, Telecommunications and Information Technology (ECTI-CON)*, 2012 9th International Conference on, IEEE, 2012, pp. 1–4.
- [20] S.M. Sze, K.K. Ng, *Physics of Semiconductor Devices*, John Wiley & Sons, 2006.
- [21] M.E. Aydın, N. Yıldırım, A. Türüt, Temperature-dependent behavior of Ni/4H-nSiC Schottky contacts, *J. Appl. Phys.* 102 (4) (2007) 043701.
- [22] S.M. Tunhuma, F.D. Aurret, M.J. Legodi, M. Diale, The effect of high temperatures on the electrical characteristics of Au/n-GaAs Schottky diodes, *Physica B* 480 (2016) 201–205.
- [23] J.H. Werner, H.H. Güttler, Temperature dependence of Schottky barrier heights on silicon, *J. Appl. Phys.* 73 (3) (1993) 1315–1319.
- [24] J.H. Werner, H.H. Güttler, Barrier inhomogeneities at Schottky contacts, *J. Appl. Phys.* 69 (3) (1991) 1522–1533.
- [25] S. Chand, J. Kumar, Current transport in Pd2Si/n-Si(100) Schottky barrier diodes at low temperatures, *Appl. Phys. A* 63 (2) (1996) 171–178.